

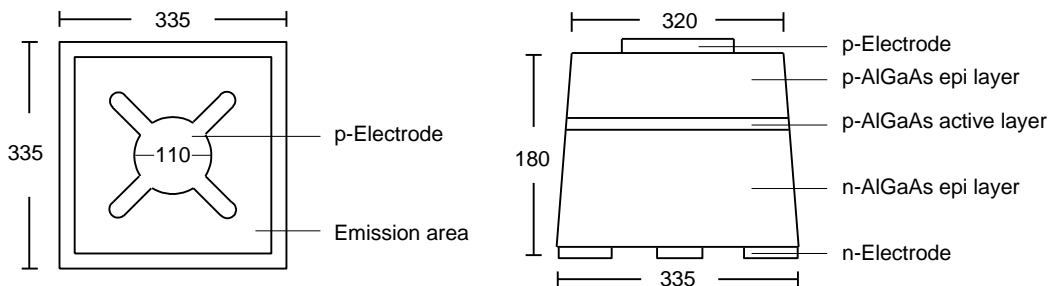
■ **Features :**

- AlGaAs/AlGaAs Wafer
- Very High Power
- High Speed
- High Performance
- Superior Thermal Stability

■ **Typical Applications :**

- IrDA
- Encoder
- Data Communication

■ **Outline Dimensions : (Unit: um)**



■ **Physical Structure :**

Chip dimension	Chip size	335 um x 335 um
	Thickness	180 um
	Emission area	320 um
	Bonding pad	110 um
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ **Electro-Optical Characteristics : (Ta = 25°C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _F	I _F = 50 mA	-	1.46	1.80	V
		I _F = 200 mA	-	1.74	2.30	
Reverse Voltage	V _R	I _R = 10 uA	5	-	-	V
Wavelength	λ _P	I _F = 50 mA	-	850	-	nm
Spectral width at half height	Δλ	I _F = 50 mA	-	40	-	nm
Radiant Power	P _o	I _F = 20 mA	1.00	2.00	-	mW
Rise / Fall Time	t _r / t _f	I _F = 50 mA	-	25 / 15	35 / 35	ns

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

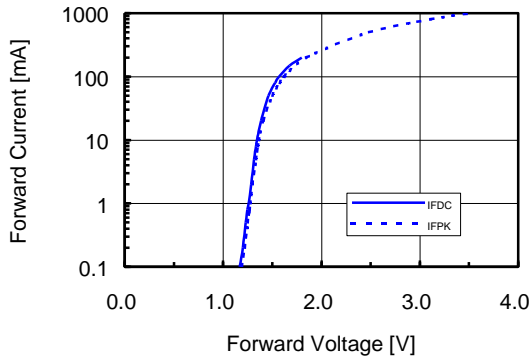


Fig 2. Relative Radiant Power vs. Wavelength

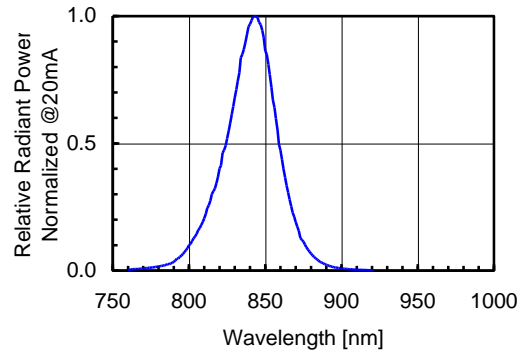


Fig 3. Relative Radiant Power vs. Forward DC Current

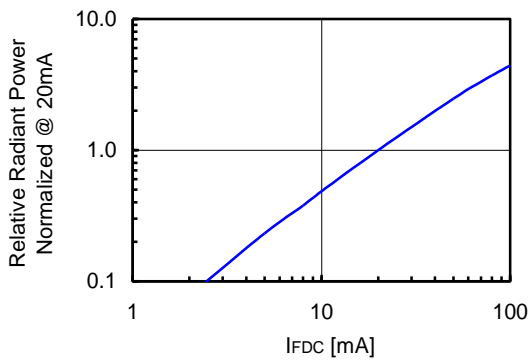


Fig 4. Relative Radiant Power vs. Forward Peak Current

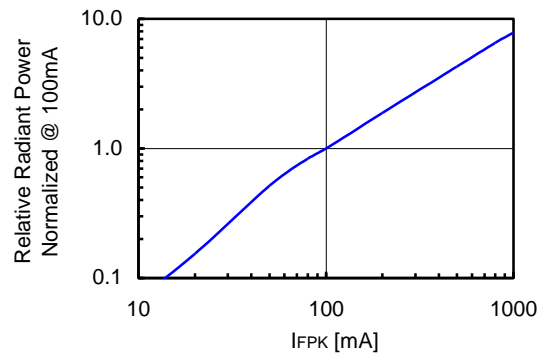


Fig 5. Forward DC Voltage vs. Temperature

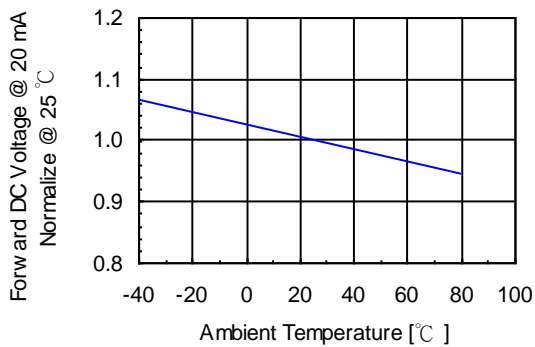


Fig 6. Relative Radiant Power vs. Temperature

